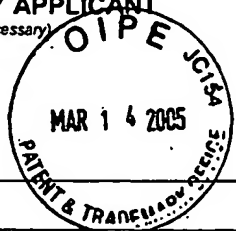


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First Named Inventor	Ahn, Kie
Group Art Unit	2823
Examiner Name	Toledo, Fernando

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Application Number	10/602,323
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Group Art Unit	2823
Examiner Name	Toledo, Fernando

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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Application Number	10/602,323
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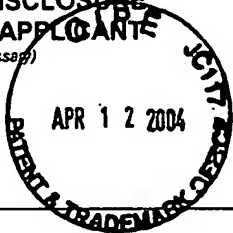
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First Named Inventor Ahn, Kie

Group Art Unit 2812

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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<i>[Signature]</i>		AARIK, JAAN , et al., "Influence of substrate temperature on atomic layer growth and properties of HfO/sub 2/ thin films", <u>Thin Solid Films</u> , 340(1-2), (1999), 110-116	

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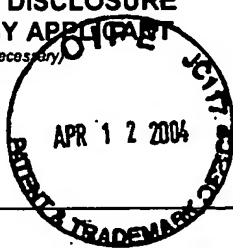
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